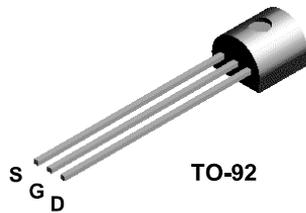


BF244A
BF244B
BF244C



N-Channel RF Amplifier

This device is designed for RF amplifier and mixer applications operating up to 450 MHz, and for analog switching requiring low capacitance. Sourced from Process 50.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{DG}	Drain-Gate Voltage	30	V
V _{GS}	Gate-Source Voltage	- 30	V
I _D	Drain Current	50	mA
I _{GF}	Forward Gate Current	10	mA
T _{stg}	Storage Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BF244A / BF244B / BF244C	
P _D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W